



TO-92L Plastic-Encapsulate Transistors

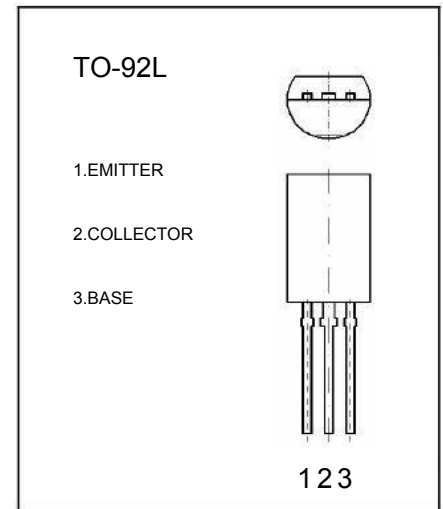
C2634 TRANSISTOR (NPN)

FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with A1127

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	55	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current – Continuous	0.2	A
P_C	Collector Power Dissipation	0.4	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	55			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$		1	100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=2\text{mA}$	180		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CB}=5\text{V}, I_E=2\text{mA}$ $f=200\text{MHz}$		200		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T
Range	180-360	260-520	360-700